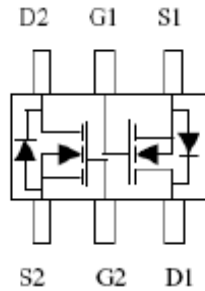
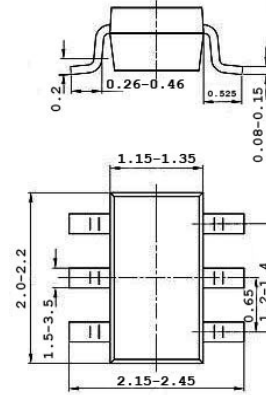


MOSFET (N-CHANNEL)
Plastic-Encapsulate Transistor
FEATURES

- Dual N-channel MOSFET
- Low on-resistance
- Low gate threshold voltage
- Low input capacitance
- Fast switching speed
- Low input/output leakage


MARKING: K72
SOT-363


UNIT:mm

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

MAXIMUM RATINGS

Parameters	Symbols	Value	UNITS
Drain-Source Voltage	V_{DSS}	60	V
Drain-Gate Voltage	V_{DGR}	60	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current	I_D	115	mA
Total Power Dissipation	P_D	200	mW
Junction and Storage Temperature	T_J, T_{stg}	-55~150	°C

ELECTRICAL CHARACTERISTICS

Parameters	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Drain-Source Breakdown Voltage*	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=10\mu A$	60	70		V
Gate-Threshold Voltage*	$V_{th(GS)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.5	2	
Gate-Body Leakage*	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 10	nA
Zero Gate Voltage Drain Current*	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$ $V_{DS}=60V, V_{GS}=0V, T_j=125$			1 500	μA
On-State Drain Current*	$I_{D(ON)}$	$V_{GS}=10V, V_{DS}=7.5V$	500	1000		mA
Drain-Source On-Resistance*	$r_{DS(ON)}$	$V_{GS}=5V, I_D=50mA$ $V_{GS}=10V, I_D=500mA$		3.2 4.4	7.5 13.5	Ω
Forward Tran Conductance*	g_{fs}	$V_{DS}=10V, I_D=200mA$	80			ms
Input Capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0V, f=1MHz$		22	50	pF
Output Capacitance	C_{OSS}		11	25		
Reverse Transfer Capacitance	C_{RSS}		2	5		

SWITCHING

Turn-on Time	$t_{d(on)}$	$V_{DD}=30V, R_L=150\Omega,$ $I_D=200mA, V_{GEN}=10V,$ $R_G=25\Omega$		7	20	ns
Turn-off Time	$t_{d(off)}$			11	20	

 *Pulse test, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$

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